NCE N-Channel Super Trench Power MOSFET

Description

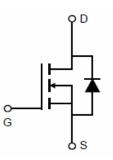
The NCEP30T21GU uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

- $V_{DS} = 30V$, $I_D = 210A$ $R_{DS(ON)} = 1m\Omega$ (typical) @ $V_{GS} = 10V$ $R_{DS(ON)} = 1.25m\Omega$ (typical) @ $V_{GS} = 4.5V$
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

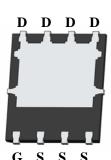
Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Schematic Diagram





Top View

Bottom View

100% UIS TESTED!

100% AVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP30T21GU	NCEP30T21GU	DFN5X6-8L	-	-	-

Absolute Maximum Ratings (T_C=25°Cunless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	30	V	
Gate-Source Voltage	V _G S	±20	V	
Drain Current-Continuous (Silicon Limited)	I _D	210	А	
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	160	А	
Pulsed Drain Current (Package Limited)	I _{DM}	450	А	
Maximum Power Dissipation	P _D	100	W	
Derating factor		0.80	W/℃	
Single pulse avalanche energy (Note 5)	E _{AS}	1800	mJ	
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 150	$^{\circ}$	



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Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	R ₀ JC	1.25	°C/W	1
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	30		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.5	2.0	V
Drain-Source On-State Resistance	Б	V _{GS} =10V, I _D =100A	-	1.0	1.15	mΩ
	R _{DS(ON)}	V _{GS} =4.5V, I _D =100A	-	1.25	1.5	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =100A		90	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	7150	-	PF
Output Capacitance	Coss		-	2400	-	PF
Reverse Transfer Capacitance	C _{rss}	r=1.0WIn2	-	119	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V_{DD} =15V, I_{D} =100A V_{GS} =10V, R_{G} =1.6 Ω	-	13	-	nS
Turn-on Rise Time	t _r		-	8	-	nS
Turn-Off Delay Time	t _{d(off)}		-	55	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg	V _{DS} =15V,I _D =100A,	-	109	-	nC
Gate-Source Charge	Q _{gs}		-	19.1		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	11.4		nC
Drain-Source Diode Characteristics	<u> </u>		-		-	
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =100A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	210	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C, I_F = I_S$	-	35	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	120	-	nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V_DD=20V,V_G=10V,L=0.5mH,Rg=25 Ω



Typical Electrical and Thermal Characteristics

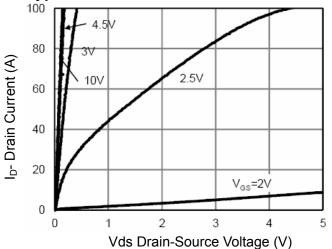


Figure 1 Output Characteristics

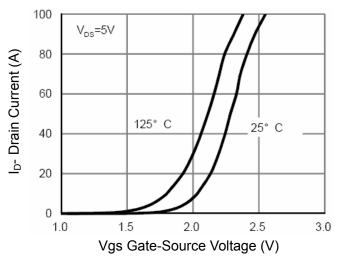


Figure 2 Transfer Characteristics

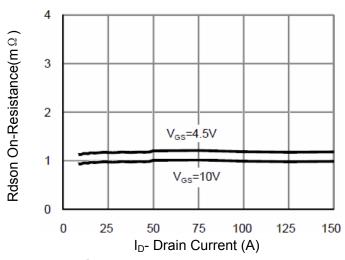


Figure 3 Rdson- Drain Current

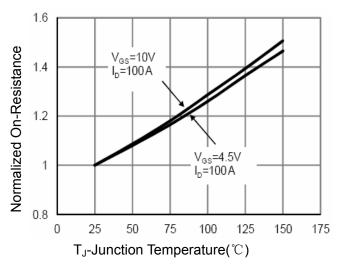


Figure 4 Rdson-Junction Temperature

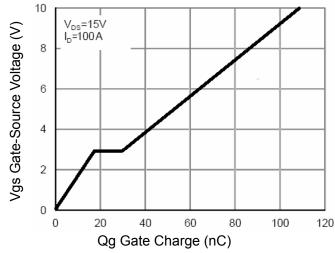


Figure 5 Gate Charge

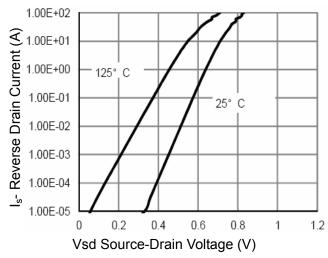


Figure 6 Source- Drain Diode Forward

NCEP30T21GU

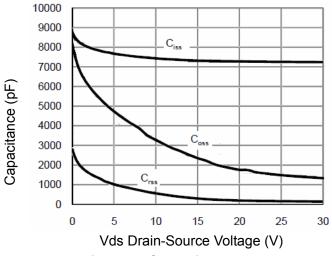


Figure 7 Capacitance vs Vds

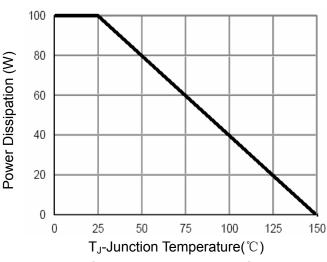


Figure 9 Power De-rating

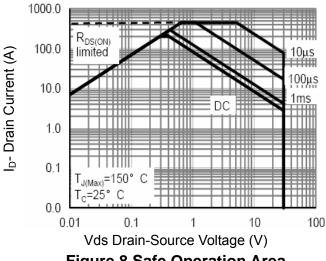


Figure 8 Safe Operation Area

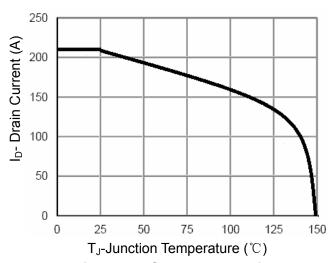


Figure 10 Current De-rating

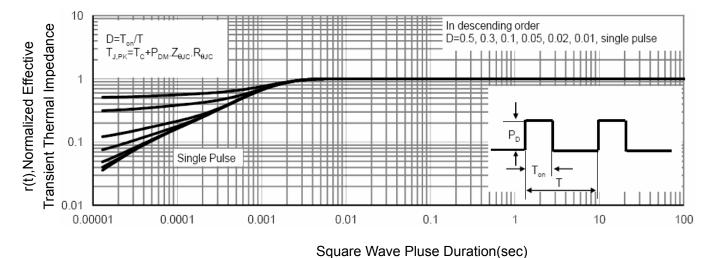
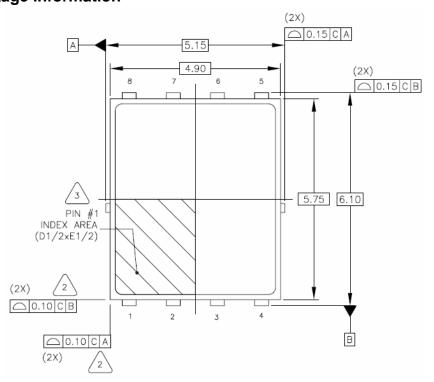
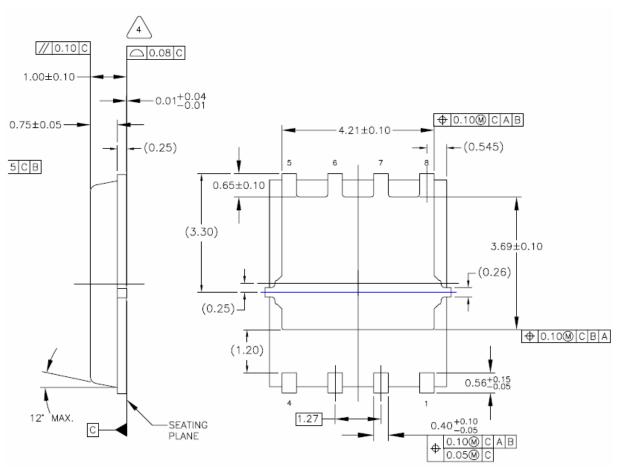


Figure 11 Normalized Maximum Transient Thermal Impedance



DFN5X6-8L Package Information







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